

field, with a field intensity less than the first field, in a wide-area region of the CMR memory film; and,

wherein includes creating a high resistance in a narrow-area region of the asymmetric-area CMR memory film in response to the second pulse includes creating a high resistance in response to a third electric field in the narrow-area region of the CMR memory film, opposite in polarity to the first field, and a fourth electric field, with a field intensity less than the third field, in a wide-area region of the CMR memory film.

[[20]] 21. (currently amended) The method of claim [[15]] 16 wherein applying [[a]] the first pulse with [[a]] the first polarity to the memory cell top electrode includes applying a positive polarity pulse;

wherein creating a low resistance in a narrow-area region of the asymmetric-area CMR memory film includes creating a low resistance in a narrow-area region adjacent the top electrode;

wherein applying [[a]] the second pulse with [[a]] the second polarity to the memory cell top electrode includes applying a negative polarity pulse; and,

wherein creating a high resistance in a narrow-area region of the asymmetric-area CMR memory film includes creating a high resistance in a narrow-area region adjacent the top electrode.

²²
21-34. Canceled